

KSB13003CR



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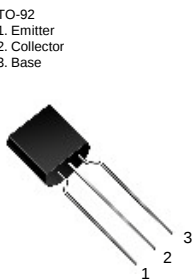
High Voltage Switch Mode Application

- High voltage, High speed power switching
- Suitable for Electronic Ballast up to 21W

Absolute Maximum Ratings TC=25℃ unless otherwise noted

1.5 Amperes
NPN Silicon Power Transistor
1.1 Watts

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	800	V
Collector-Emitter Voltage	V_{CEO}	450	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current(DC)	I_C	1.5	A
Collector Current(Pulse)	I_{CP}	3	A
Base Current	I_B	0.75	A
Collector Dissipation(Tc=25℃)	P_C	1.10	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~150	℃



Electrical Characteristics TC=25℃ unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=500\mu A, I_E=0$	800			V
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA, I_B=0$	450			V
Emitter Cut-off Current	I_{EBO}	$V_{EB}=9.0V, I_C=0$			10	μA
*DC Current Gain	h_{FE1} h_{FE2}	$V_{CE}=10V, I_C=0.4A$ $V_{CE}=10V, I_C=1A$	20 6		40	- -
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.1A$ $I_C=1.5A, I_B=0.5A$			0.5 1.0	V V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=0.5A, I_B=0.1A$			1.0	V
Output Capacitance	C_{ob}	$V_{CB}=10V, f=0.1MHz$		21		pF
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.1A$	4			MHz
Turn on Time	t_{on}	$V_{CC}=125V, I_C=2A$ $I_{B1}=0.2A, I_{B2}=-0.2A$ $R_L=125\Omega$			1.1	μs
Storage Time	t_{stg}				4.0	μs
Fall Time	t_F				0.7	μs

* Pulse Test: Pulse Widths $\leq 300\mu s$, Duty Cycles $\leq 2\%$

Note.

hFE1 Classification	R	20 ~ 30
	O	25 ~ 35
	Y	30 ~ 40

Package Mark information.

S	CR	S	SemiHow Symbol
13003	YWW	YWW	Y; year code, WW; week code
YWW	Z	Z	hFE1 Classification

Typical Characteristics

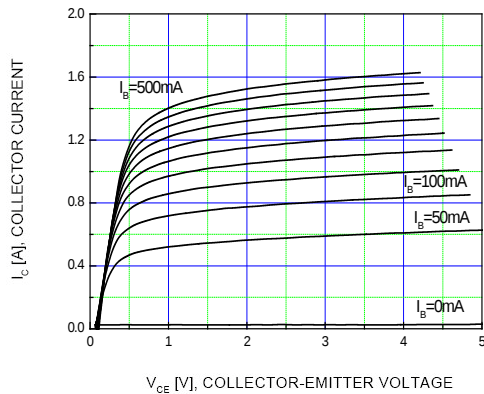


Figure 1. Static Characteristic

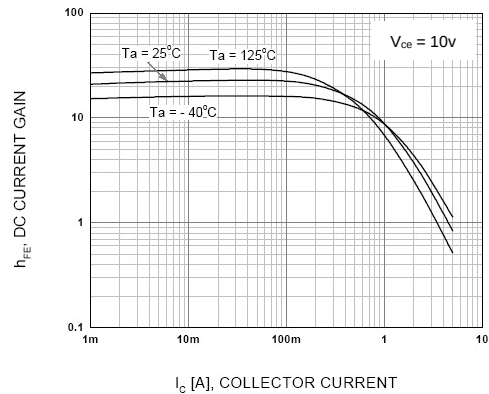


Figure 2. DC current Gain

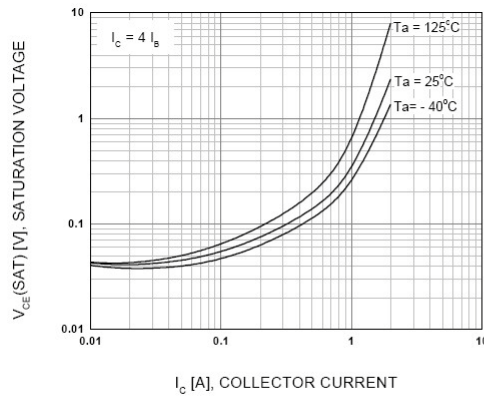


Figure 3. Collector-Emitter Saturation Voltage

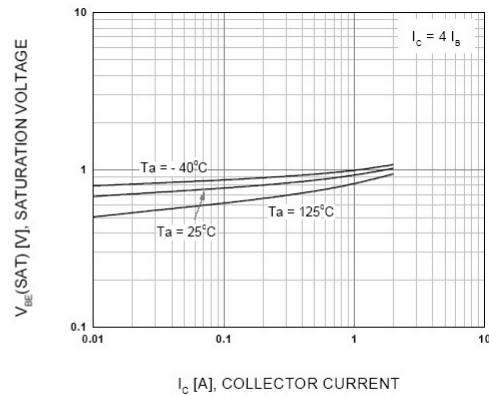


Figure 4. Base-Emitter Saturation Voltage

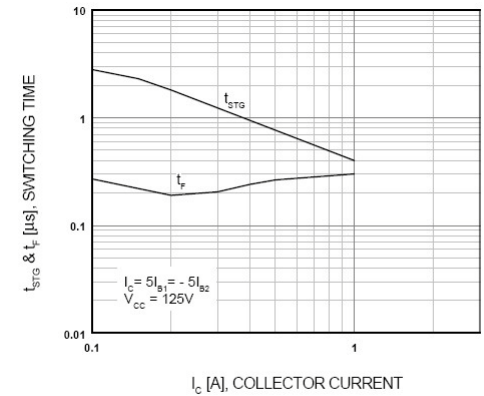


Figure 5. Resistive Load Switching Time

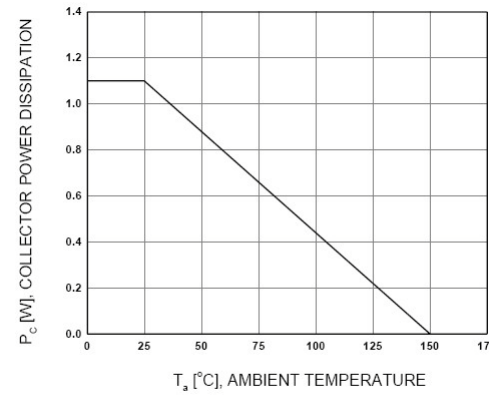


Figure 6. Power Derating

Typical Characteristics

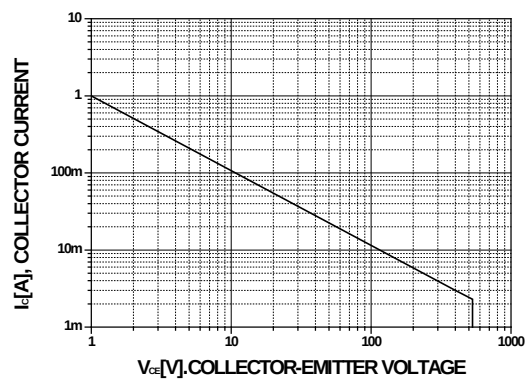


Figure 7. Forward Bias Safe Operating Area

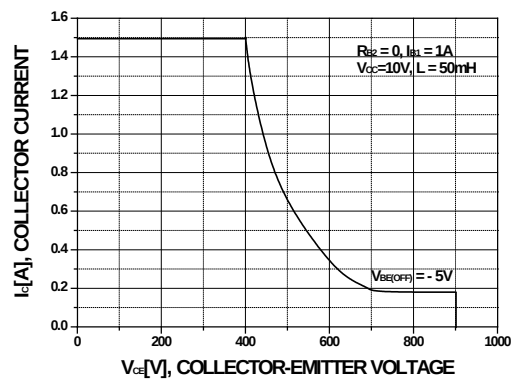
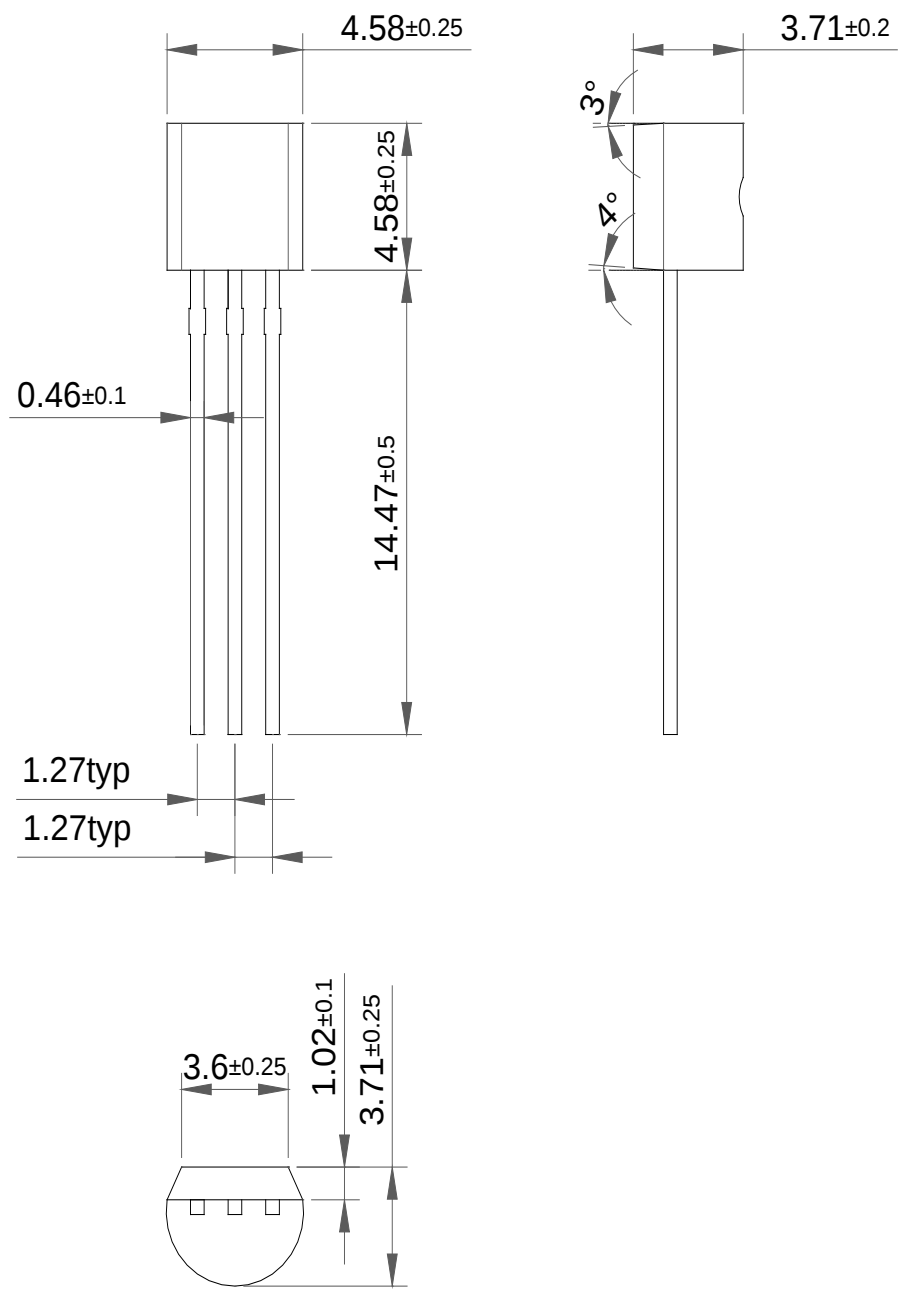


Figure 8. Reverse Bias Safe Operating Area

Package Dimension

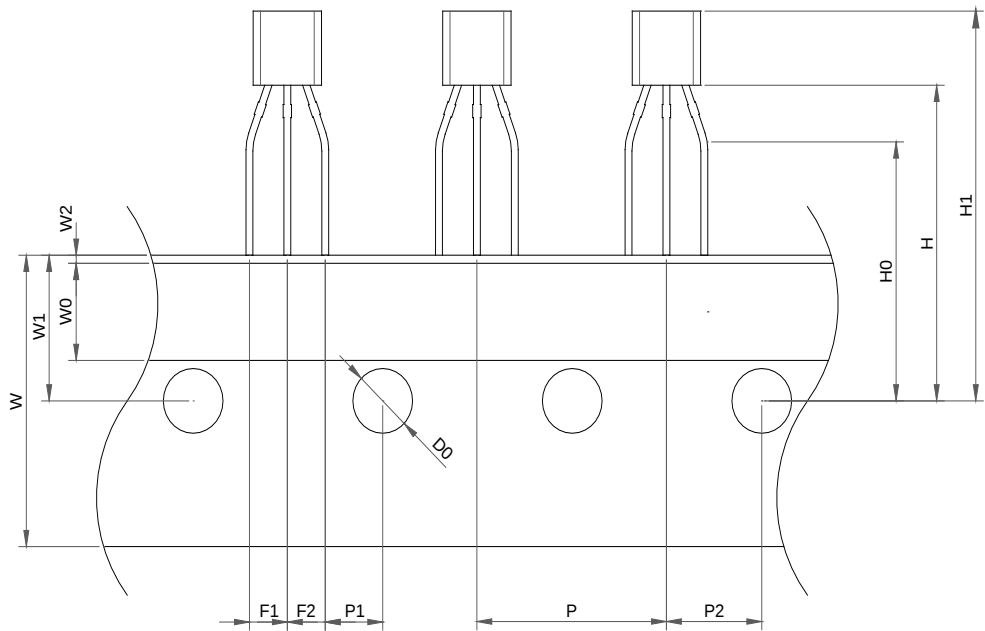
TO-92



Dimensions in Millimeters

Package Dimension

TO-92 TAPING



Item	Symbol	Dimension [mm]	
		Reference	Tolerance
Component pitch	P	12.7	±0.5
Side lead to center of feed hole	P1	3.85	±0.5
Center lead to center of feed hole	P2	6.35	±0.5
Lead pitch	F1,F2	2.5	+0.2/-0.1
Carrier Tape width	W	18.0	+1.0/-0.5
Adhesive tape width	W0	6.0	±0.5
Tape feed hole location	W1	9.0	±0.5
Adhesive tape position	W2	1.0 MAX	
Center of feed hole to bottom of component	H	19.5	±1
Center of feed hole to lead form	H0	16.0	±0.5
Component height	H1	27.0 max	
Tape feed hole diameter	D0	4.0	±0.2